

**MEMS: Fabrication:**

# Microstereolithography



Prasanna S. Gandhi  
Assistant Professor,  
Department of Mechanical Engineering,  
Indian Institute of Technology, Bombay,



# Recap

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- Optical characterization
- Previous classes on fabrication
  - VLSI based methods
    - Patterning
    - Etching
    - Deposition
  - EDM
  - ECM
  - Laser machining

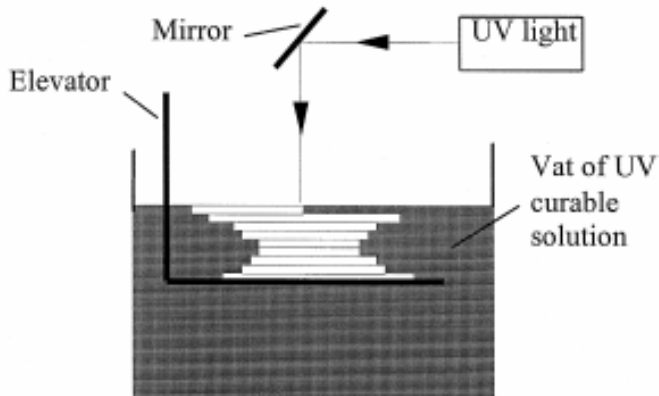
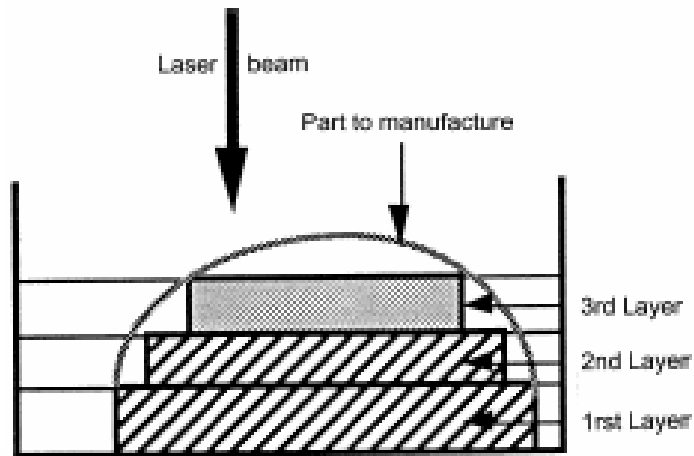


# Today's Class

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- Microstereolithography
  - Advantages
  - Fundamentals of laser optics
  - Methods
    - Projection method
    - Scanning method
  - Some fundamentals of polymerization

# What is Microstereolithography?



- Novel microfabrication process for fabricating high aspect ratio and complex 3D microstructures.
- Evolved from the rapid prototyping industry.
- UV laser beam scanned on a photopolymerizable resin.
- Curing of the resin layer by layer.
- Stacking of all the layers.



# Motivation

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## **Need for Microstereolithography**

### **MEMS – Worldwide Research attention**

- Requirement of current actuating and sensing mechanisms to be of complex 3D shapes.
- Incorporation of a wide range of materials

### **Limitations of Conventional processes :**

- Inability to manufacture high aspect ratio and complex 3D microstructures.
- Few semiconductors and other materials processed by current VLSI-based machining processes for MEMS.



# Microstereolithography

## Process Types

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- Scanning method:
  - Scan one layer by focused laser beam and then the next layer
- Dynamic mask method:
  - Expose the layer to be built at a time
  - Change the mask dynamically
  - Expose the next layer

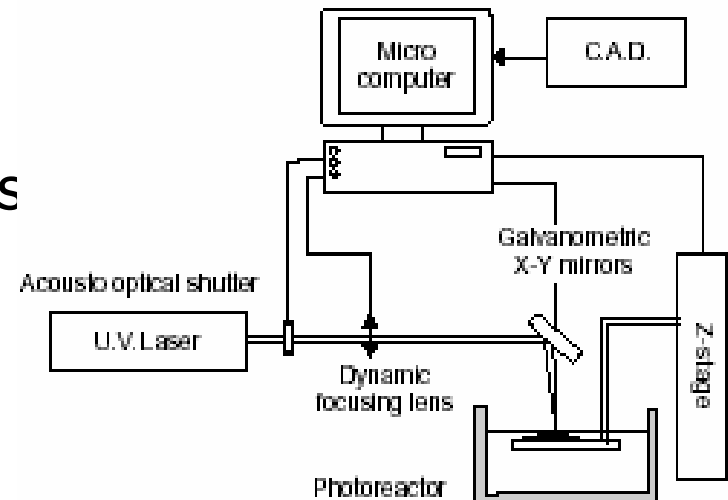
# Scanning Method

## ■ Classical msl

- Focusing by a dynamic lens
- Use of galvanometric mirrors
- Theoretical best point of focus not intersecting the resin surface.

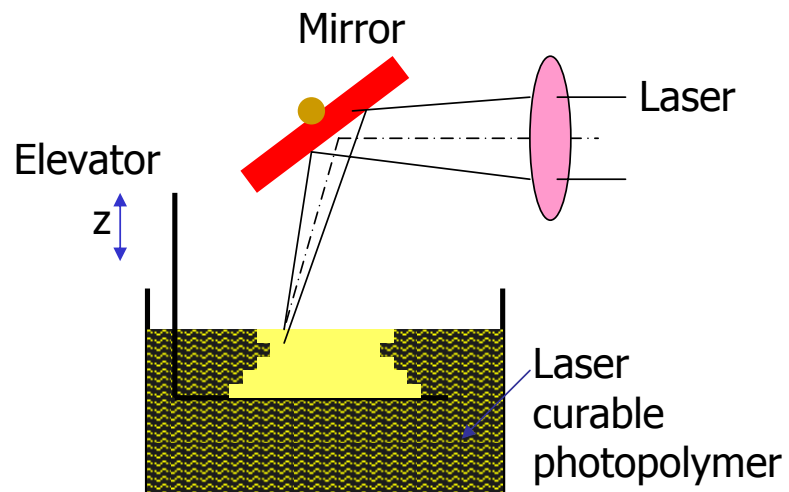
## ■ Free surface technique

- All optical parts fixed
- X-Y-Z motorized translation stage
- Thickness control of deposited liquid layer difficult

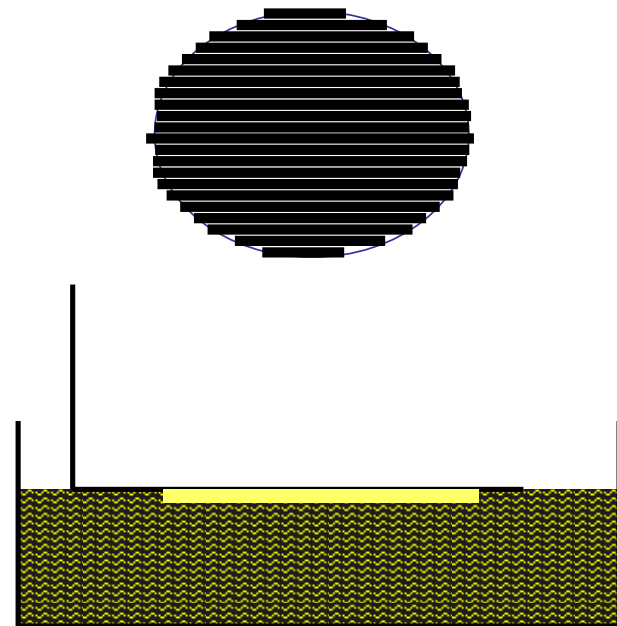


# Scanning Method

- Schematic diagram



## Vector Scan







# Scanning Method

## Issues

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- Factors affecting resolution of components:
  - Laser intensity
  - Motion and quality of the beam
  - Photopolymer/ monomer used
  - Focusing
  - Exposure
- In case of ceramic materials process of laser sintering is used



# Scanning Method

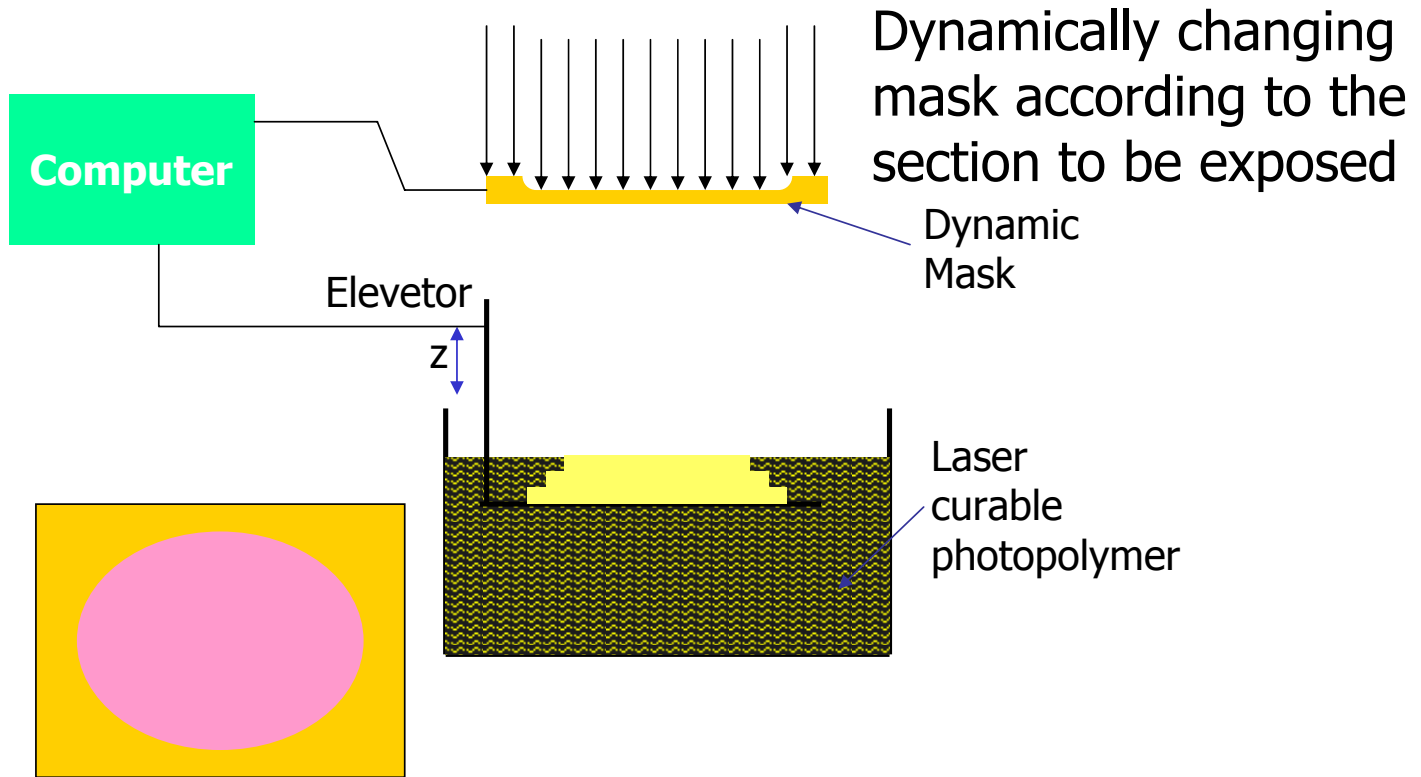
## Variations

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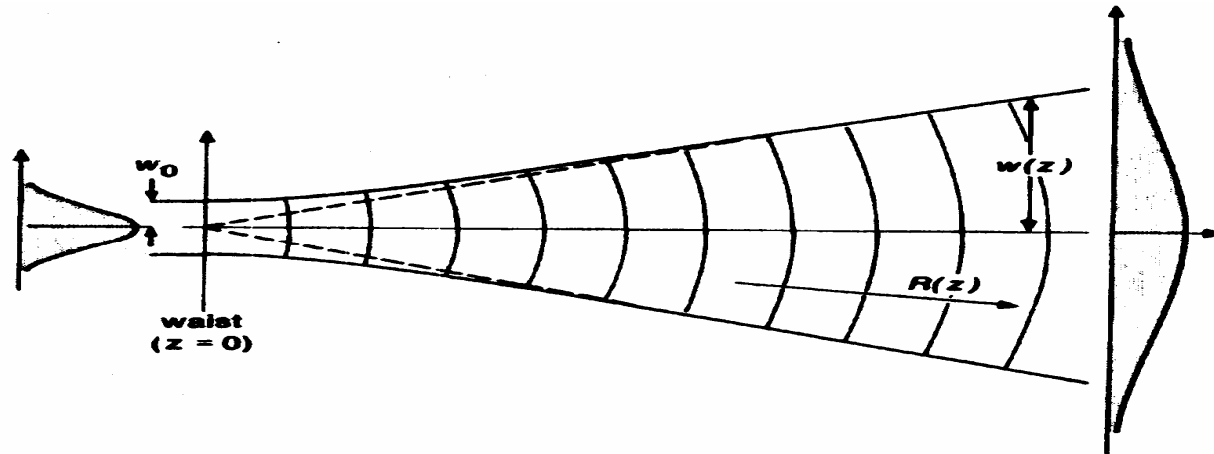
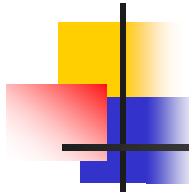
1. Fixed optics, move liquid tank for xy scanning
2. Various ways for scanning
  - Rotating galvano-scanning mirrors
  - Linearly moving mirrors
  - Raster scan vs vector scan

# Microstereolithography

## Dynamic mask process



# Fundamentals of Laser Beam



## Gaussian Beams

Beam waist at  $z = 0$ , where the spot size is  $w_0$ .  
Expansion to  $w = w(z)$  with distance  $z$  away from the laser.

The beam radius of curvature,  $R(z)$ , also increases with distance far away.



# Fundamentals of Laser Beam

Expressions for spot size, radius of curvature,

$$w(z) = w_0 \sqrt{1 + (z/z_R)^2}$$

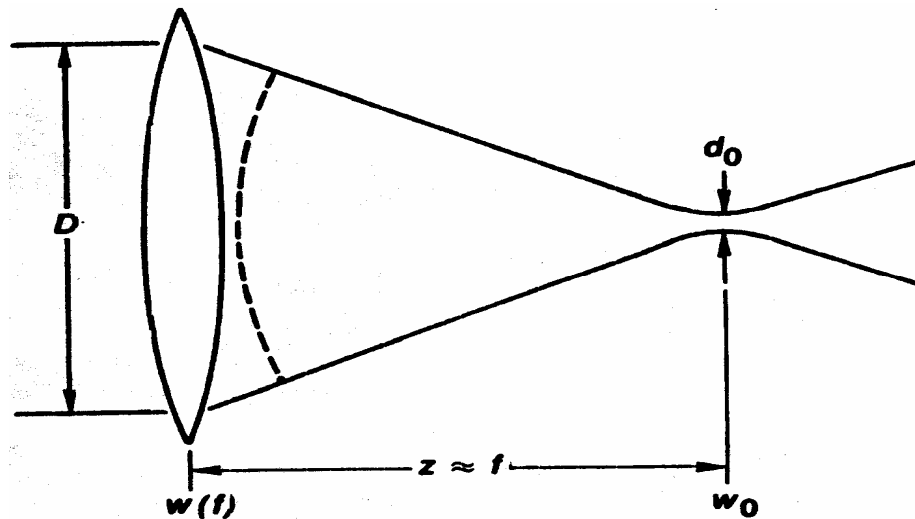
$$R(z) = z + z_R^2 / z$$

where  $z_R$  is the Rayleigh Range (the distance over which the beam remains about the same diameter), and it's given by:

$$z_R \equiv \pi w_0^2 / \lambda$$

# Fundamentals of Laser Beam

Gaussian  
Beam  
Focusing



Airy Disk formula for spot size:

$$d = 2.44\lambda (F / D)$$



# System Details

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## Typical System Components

- Laser
- Beam delivery system
- Computer controlled precision stages and a CAD design tool
- Process monitoring system with a CCD camera.
- UV curable resin – HDDA (1,6 – Hexanediol diacrylate)



# Laser

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- UV Lamps
- He-Cd Laser
- Argon Ion Laser

## Typical specifications :

Name of the supplier : Coherent Inc.

Product model : Innova 300 Series (I-304) (Ar<sup>+</sup> Laser)

Multiline UV wavelengths : 333.4nm to 363.8nm

Power : 200mW

Diameter (@ 1/e<sup>2</sup> points) in mm : 1.5mm

Divergence (full angle) in mrad : 0.5





# UV- curable Resin

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## Desired Properties:-

- Photosensitivity at the operating wavelength
- Low viscosity to produce a smooth surface
- High curing speed
- Low shrinkage during polymerization
- High absorption for low penetration of light.

## Types of Resins

1) Epoxy Resins

2) Acrylate resins

HDDA (1,6 – Hexanediol diacrylate) with 4% by wt. photoinitiator

# Spot characterization using Oslo

Argon Ion laser Edm NT45-113 [Argon3a] - OSLO LT

File Lens Evaluate Optimize Tolerance Source Tools Window Help

Surface Data

Gen Setup Wavelengths Variables Draw On Group Notes

Lens: Argon Ion laser Edm NT45-113 Efl 5.288550

Ent beam radius 0.750000 Field angle 5.7296e-05 Primary wavln 0.364000

SRF	RADIUS	THICKNESS	APERTURE RADIUS	GLASS	SPECIAL
OBJ	0.000000	1.0000e+20	1.0000e+14	AIR	
1	3.100000	3.450000	2.500000	BK7	C
2	-20.450000	0.000000	2.500000	AIR	
AST	0.000000	0.000000	0.458573	AIR	C
4	0.000000	0.000000	0.458573	AIR	
IMS	0.000000	3.233582	5.2886e-06		

Autodraw

Argon Ion laser Edm NT45-113  
OPTICAL SYSTEM LAYOUT

UNITS: MM  
DES: OSLO

1.01

UW 1 - Spot Diagram Analysis \*

FULL FIELD  
5.73e-05deg

0.7 FIELD  
4.01e-05deg

ON-AXIS  
0deg

-0.05 -0.025 0 0.025 0.05

# Mathematical Modeling

- Laser exposure along the X-Axis defined as

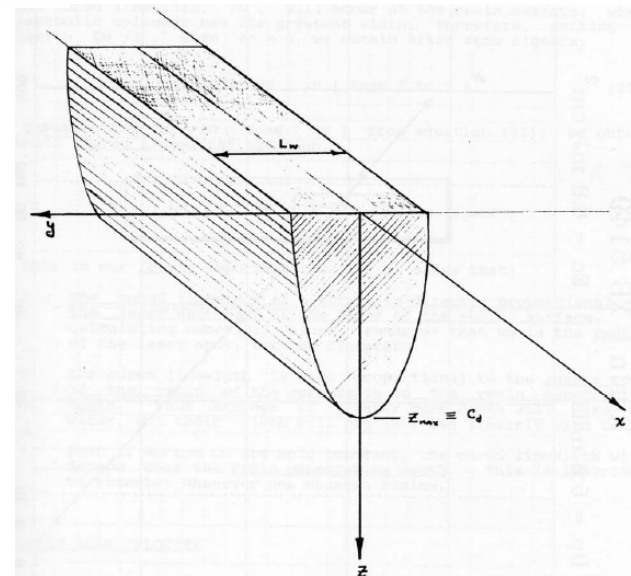
$$E(y, z) = \sqrt{\frac{2}{\pi}} \left( \frac{P}{W_0 V_s} \right) e^{\left( \frac{-2y^2}{W_0^2} \right)} e^{-\left( \frac{z}{D_p} \right)}$$

- Curing depth working equation :

$$C_d = D_p \ln\left(\frac{E_{max}}{E_c}\right)$$

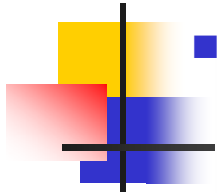
- Cured Line width:

$$L_w = \sqrt{2} W_0 \left( \ln\left(\frac{E_{max}}{E_c}\right) \right)^{0.5}$$



# Mathematical Modeling

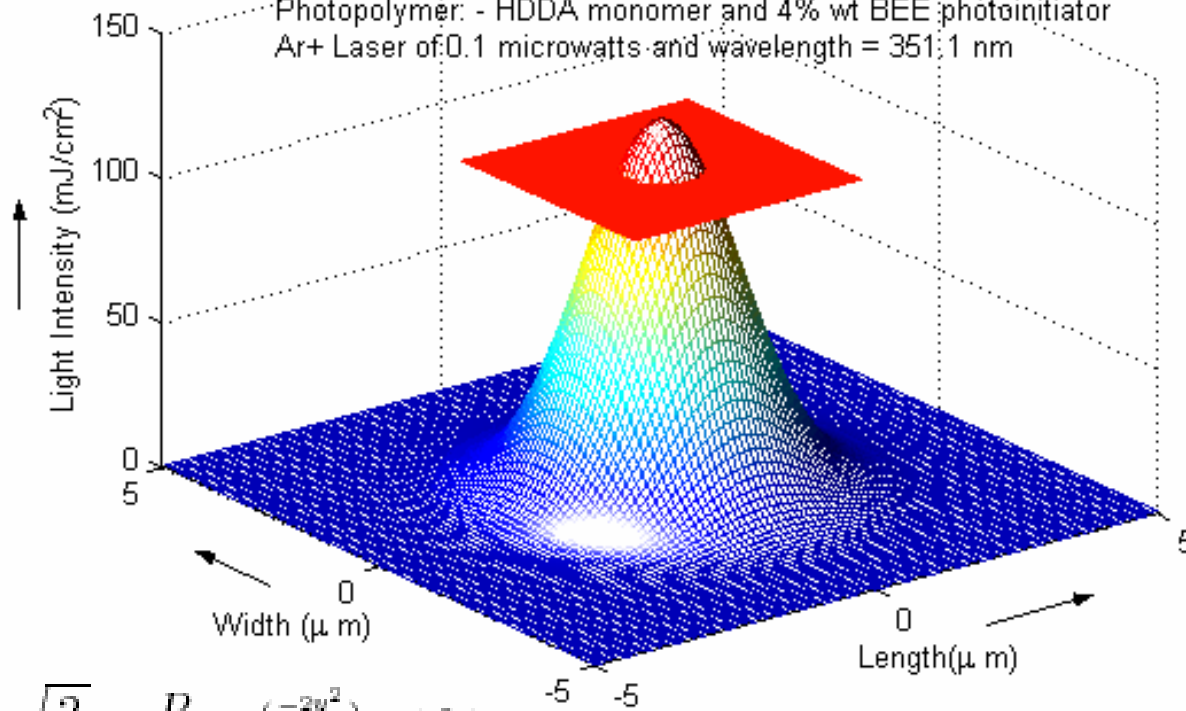
- Laser exposure along the X-Axis defined as



Gaussian Light Intensity Distribution

Rectangle shows Maximum Energy ( $E_c=1110 \text{ J/m}^2$ ) required for Curing of photopolymer

Photopolymer: - HDDA monomer and 4% wt BEE photoinitiator  
Ar+ Laser of 0.1 microwatts and wavelength = 351.1 nm



$$E(y, z) = \sqrt{\frac{2}{\Pi}} \left( \frac{P}{W_0 V_s} \right) e^{\left( \frac{-2y^2}{W_0^2} \right)} e^{-\left( \frac{z}{D_p} \right)}$$



# Microstereolithography

## Limitations

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- Smooth 3D surfaces difficult to produce; stepping effects will always be present
- Mass production of several components is another challenge
- Extremely small features difficult to produce



# Conclusions

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- Microstereolithography: process details
- Mainly a process for true 3D structures of polymer and ceramic materials
- Limitation about the size of the feature
- Any suggestions to improve E-beam with z-stage movement



# Mathematical Modeling

$$E(y, z) = \int H(x, y, z) dx / V_s \approx \frac{e^{-\frac{z}{D_P}}}{V_s} \sum H(x, y, 0) \Delta x$$

- Exposure (Energy per unit area)

$$LSF(y) = \int_{-\infty}^{+\infty} H(x, y) dx$$

- Line Spread Function (LSF)

$$E(y, z) = \frac{a LSF(y) e^{-\frac{z}{D_P}}}{V_s}$$

- Modified expression for exposure:

$$z^* = D_P \ln \left( \frac{a LSF(y^*)}{V_s E_c} \right)$$